

METHOD OF PROCESSING SUBSTRATE, METHOD OF MANUFACTURING
SEMICONDUCTOR DEVICE, PROGRAM, AND SUBSTRATE PROCESSING
APPARATUS

ABSTRACT

There is provided a technique that includes (a) preparing a substrate including a first surface, which includes a first termination and constitutes at least a portion of an inner surface of a recess, and a second surface, which includes a second termination different from the first termination, and (b) removing the first termination selectively with respect to the second termination by exposing the substrate to a processing solution containing a liquid that reacts with the first termination and an additive that reduces surface tension of the liquid.

Fig. 4